

**The RF Line**

**NPN SILICON RF POWER TRANSISTORS**

... designed primarily for high-voltage applications as a high-power linear amplifier from 2.0 to 30 MHz. Ideal for marine and base station equipment.

- Specified 50 Volt, 30 MHz Characteristics —  
 Output Power = 150 W(PEP)  
 Minimum Gain = 13 dB  
 Efficiency = 45%
- Intermodulation Distortion ( $\alpha$  150 W(PEP) —  
 IMD = -32 dB (Max)
- Diffused Emitter Resistors for Superior Ruggedness
- 100% Tested for Load Mismatch at all Phase Angles with 30:1 VSWR ( $\alpha$  150 W CW)

MAXIMUM RATINGS			
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CE0}$	50	Vdc
Collector-Base Voltage	$V_{CB0}$	100	Vdc
Emitter-Base Voltage	$V_{EB0}$	4.0	Vdc
Collector Current — Continuous	$I_C$	16	Adc
Withstand Current — 10 s	—	20	Adc
Total Device Dissipation ( $\alpha$ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ )	$P_D$	233 1.33	Watts W/°C
Storage Temperature Range	$T_{stg}$	- 65 to +150	°C

MRF429MP is for ordering an hfc matched pair.

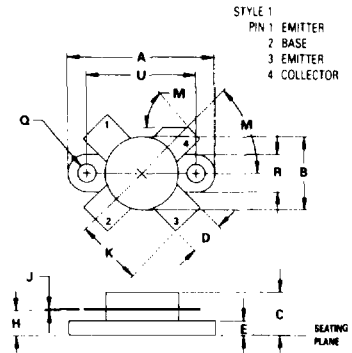
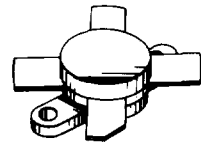
THERMAL CHARACTERISTICS			
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.75	°C/W

**MRF429**  
**MRF429MP**

150 W (LINEAR) 30 MHz

**RF POWER TRANSISTORS**

**NPN SILICON**



NOTES  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982  
 2. CONTROLLING DIMENSION INCH

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	24.39	25.14	0.960	0.990
B	11.82	12.95	0.465	0.510
C	5.82	6.96	0.229	0.275
D	5.49	5.96	0.216	0.235
E	2.14	2.79	0.084	0.110
H	3.66	4.52	0.144	0.178
J	0.08	0.17	0.003	0.007
K	11.05	—	0.435	—
M	45	NOM	45	NOM
Q	2.93	3.30	0.115	0.130
R	6.25	6.47	0.246	0.255
U	18.29	18.54	0.720	0.730

CASE 211-11

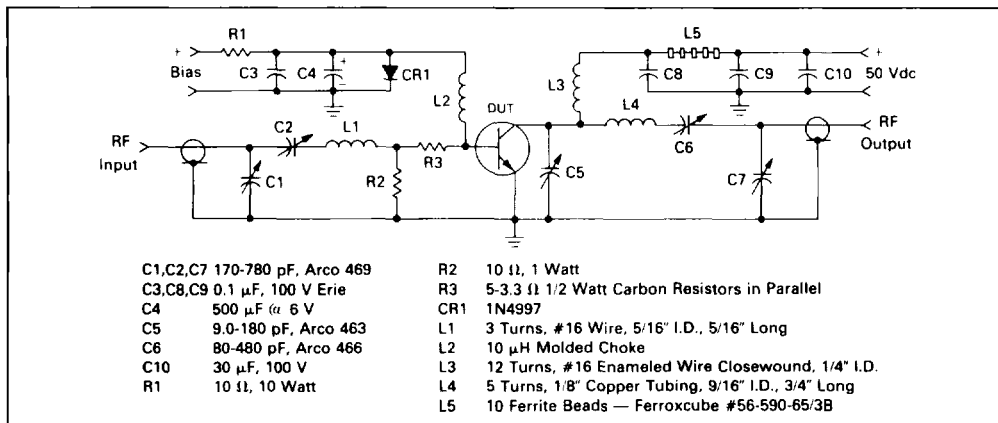
# MRF429, MRF429MP

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 200 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	—	—	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 100 mA, V <sub>BE</sub> = 0)	V <sub>(BR)CES</sub>	100	—	—	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 100 mA, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	100	—	—	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 mA, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	4.0	—	—	Vdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain (I <sub>C</sub> = 5.0 A, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	10	30	80	—
<b>DYNAMIC CHARACTERISTICS</b>					
Output Capacitance (V <sub>CB</sub> = 50 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	—	220	300	pF
<b>FUNCTIONAL TESTS</b>					
Common-Emitter Amplifier Gain (V <sub>CC</sub> = 50 Vdc, P <sub>out</sub> = 150 W (PEP), I <sub>C(max)</sub> = 3.32 A, f = 30; 30.001 MHz)	G <sub>PE</sub>	13	15	—	dB
Output Power (V <sub>CE</sub> = 50 Vdc, f = 30; 30.001 MHz)	P <sub>out</sub>	150	—	—	W (PEP)
Collector Efficiency (V <sub>CC</sub> = 50 Vdc, P <sub>out</sub> = 150 W (PEP), I <sub>C(max)</sub> = 3.32 A, f = 30; 30.001 MHz)	η	45	—	—	%
Intermodulation Distortion (1) (V <sub>CE</sub> = 50 Vdc, P <sub>out</sub> = 150 W (PEP), I <sub>C</sub> = 3.32 A)	IMD	—	35	-32	dB
Electrical Ruggedness (V <sub>CC</sub> = 50 Vdc, P <sub>out</sub> = 150 W CW, f = 30 MHz, VSWR 30:1 at all Phase Angles)	No Degradation in Output Power				

(1) To Mil Std 1311 Version A, Test Method 2204B, Two Tone, Reference Each Tone.

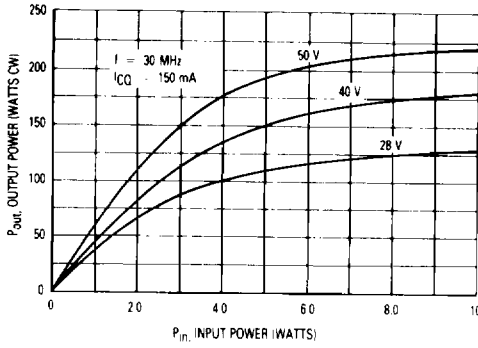
FIGURE 1 — 30 MHz TEST CIRCUIT SCHEMATIC



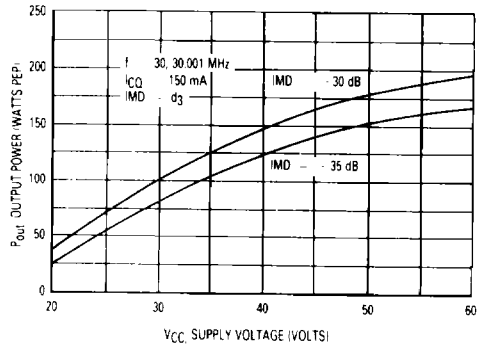
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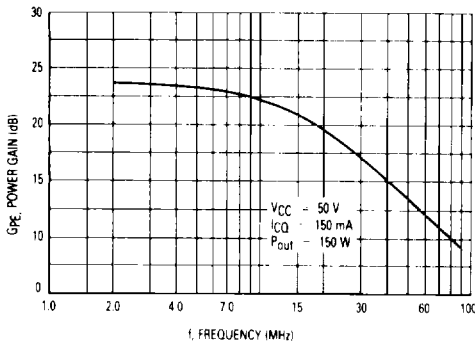
**FIGURE 2 — OUTPUT POWER versus INPUT POWER**



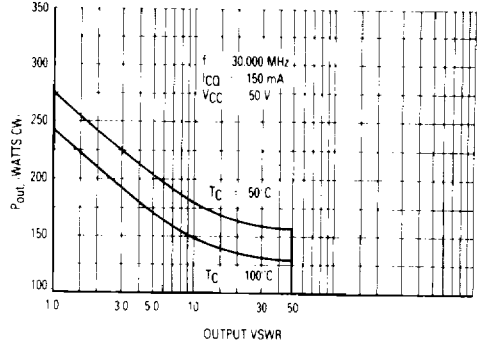
**FIGURE 3 — OUTPUT POWER versus SUPPLY VOLTAGE**



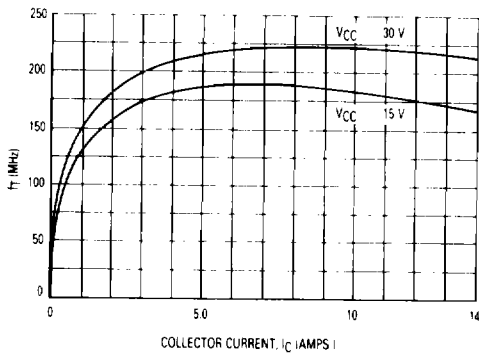
**FIGURE 4 — POWER GAIN versus FREQUENCY**



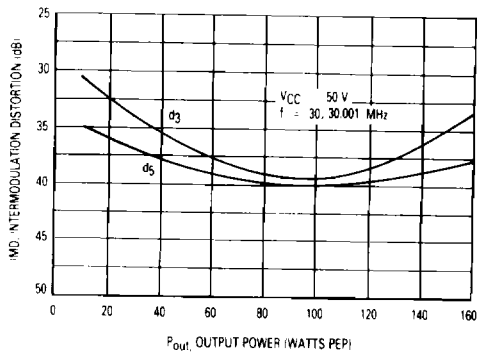
**FIGURE 5 — RF SAFE OPERATING AREA (SOAR)**



**FIGURE 6 —  $f_T$  versus COLLECTOR CURRENT**



**FIGURE 7 — IMD versus  $P_{out}$**



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FIGURE 8 — OUTPUT CAPACITANCE versus FREQUENCY

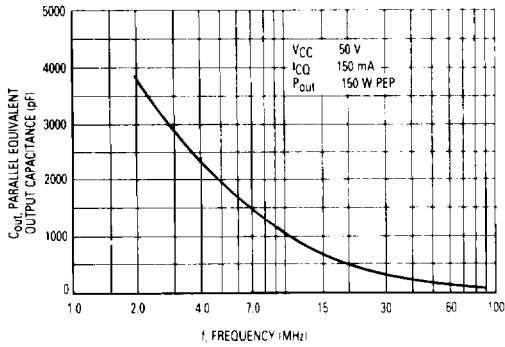


FIGURE 9 — OUTPUT RESISTANCE versus FREQUENCY

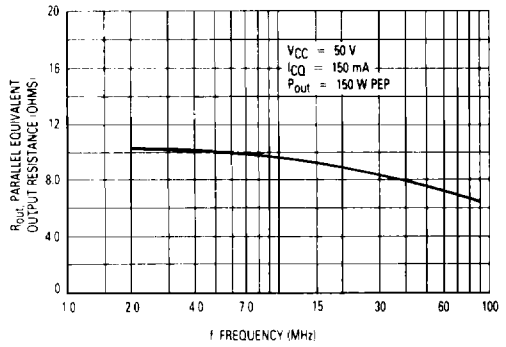


FIGURE 10 — SERIES EQUIVALENT IMPEDANCE

